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| Substitute for form 1449A/PTO                            |   |    | <b>Complete if Known</b>      |               |
| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b> |   |    | <b>Application Number</b>     | 10/582,392    |
|  |   |    | <b>Filing Date</b>            | June 28, 2007 |
|  |   |    | <b>First Named Inventor</b>   | Horsky et al. |
|  |   |    | <b>Group Art Unit</b>         | 2821          |
|  |   |    | <b>Examiner Name</b>          | Bernard Souw  |
| (use as many sheets as necessary)                        |   |    | <b>Attorney Docket Number</b> | 211843-00044  |
| Sheet  | 1 | of | 1                             |               |

| U.S. PATENT DOCUMENTS |                       |                 |                             |   |   |
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| OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS |                       |   |                |
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| Examiner Initials*                                | Cite No. <sup>1</sup> | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher city and/or country where published                                   | T <sup>2</sup> |
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| <b>Examiner Signature</b>                         |                       |   |                |

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPPE 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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